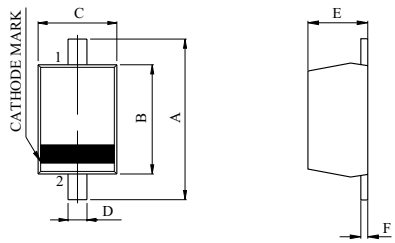
KDV269E

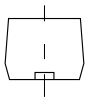
VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

CATV TUNING.

FEATURES

- High Capacitance Ratio : C2V/C25V=11.0(Min.)
- Low Series Resistance : r_S=0.75Ω(Max.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.





1. ANODE
2. CATHODE

DIM	MILLIMETERS
A	1.60±0.10
B	1.20±0.10
C	0.80±0.10
D	0.30±0.05
E	0.60±0.10
F	0.13±0.05

ESC

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	34	V
Junction Temperature	T_j	125	℃
Storage Temperature Range	T_{stg}	-55～125	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

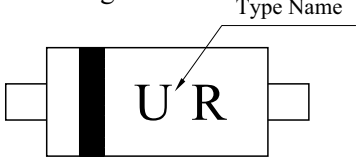
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_R	V_R=28V	-	-	10	nA
Capacitance	C_{2V}	V_R=2V, f=1MHz	29	31.5	34	pF
Capacitance	C_{25V}	V_R=25V, f=1MHz	2.5	2.75	2.9	pF
Capacitance Ratio	C_{2V}/C_{25V}		11.0	11.5	-	-
Series Resistance	r_S	V_R=5V, f=470MHz	-	-	0.75	Ω

Note : Available in matched group for capacitance to 2.0%.

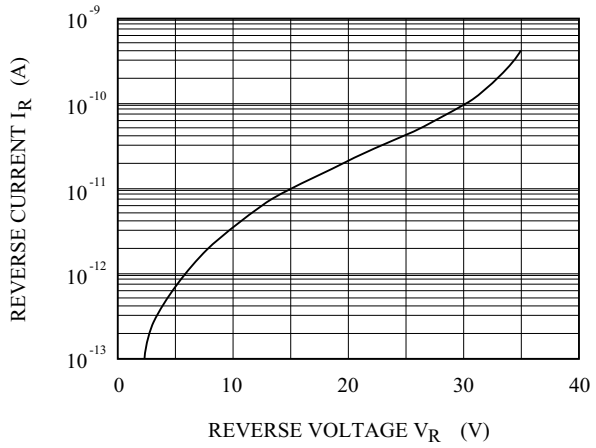
$$\frac{C(Max.)-C(Min.)}{C(Min.)} \leqq 0.02$$

(V_R=2~25V)

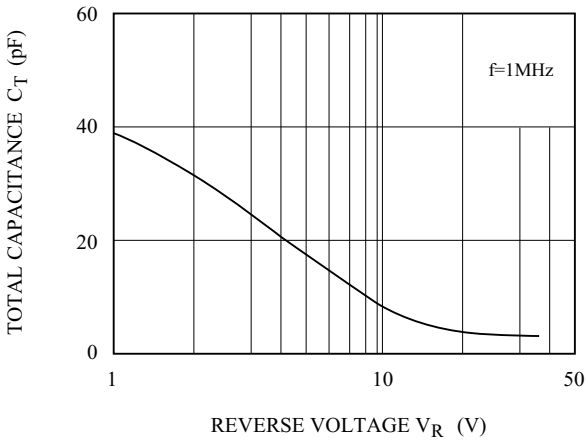
Marking



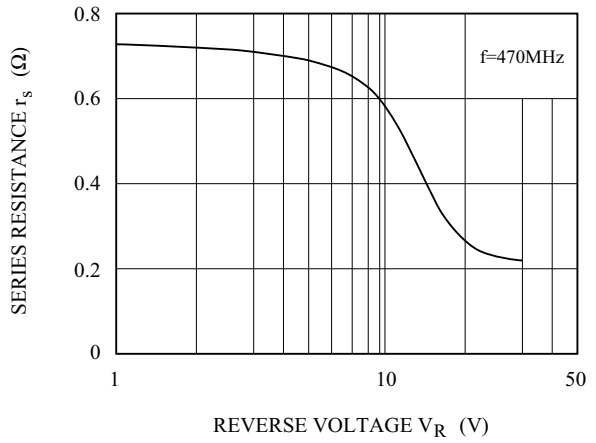
I_R - V_R



C_T - V_R



r_s - V_R



$\Delta(LOG\ C_T) / \Delta(LOG\ V_R)$ - V_R

